TOSHIBA Field Effect Transistor Silicon P Channel MOS Type (U-MOSVI)

TPC8120

Lithium Ion Battery Applications **Power Management Switch Applications**

Small footprint due to small and thin package

Low drain-source ON-resistance: RDS (ON) = 2.6 m Ω (typ.)

High forward transfer admittance: $|Y_{fs}| = 80 \text{ S}$ (typ.)

Low leakage current: $IDSS = -10 \mu A (max) (VDS = -30 V)$

Enhancement mode: $V_{th} = -0.8$ to -2.0 V ($V_{DS} = -10$ V, $I_{D} = -1$ mA)

Absolute Maximum Ratings (Ta = 25°C)

Characteri	stics	Symbol	Rating	Unit	
Drain-source voltage		V_{DSS}	-30	V	
Drain-gate voltage (Ro	$_{\rm SS} = 20 \; \rm k\Omega)$	V_{DGR}	-30	V	
Gate-source voltage		V_{GSS}	-25/+20	V	
Drain current	DC (Note 1)	ID	-18	Α	
Diain current	Pulse (Note 1)	I_{DP}	-72	A	
Drain power dissipatio	n (t = 10 s) (Note 2a)	P_{D}	1.9	W	
Drain power dissipatio	n (t = 10 s) (Note 2b)	P _D	1.0	W	
Single pulse avalanche	e energy (Note 3)	E _{AS}	211	mJ	
Avalanche current		I _{AR}	-18	Α	
Repetitive avalanche e	energy lote 2a) (Note 4)	E _{AR}	0.03	mJ	
Channel temperature		T _{ch}	150	°C	
Storage temperature ra	ange	T _{stg}	-55 to 150	°C	

Note 1, Note 2, Note 3 and Note 4: See the next page.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating

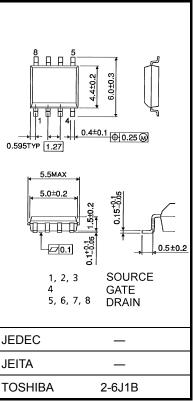
temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating

Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

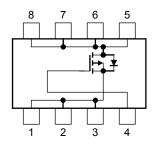
This transistor is an electrostatic-sensitive device. Handle with care.

Unit: mm



Weight: 0.080 g (typ.)

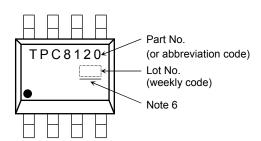
Circuit Configuration



Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to ambient (t = 10 s) (Note 2a)	R _{th (ch-a)}	65.8	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2b)	R _{th (ch-a)}	125	°C/W

Marking (Note 5)



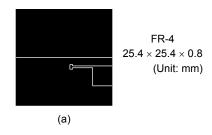
Note 6: A line under a Lot No. identifies the indication of product Labels [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

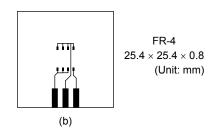
Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product. The RoHS is Directive 2002/95/EC of the European Parliament and of the Council of 27 January 2003 on the restriction of the use of certain hazardous substances in electrical and electronic equipment

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: (a) Device mounted on a glass-epoxy board (a)

(b) Device mounted on a glass-epoxy board (b)





Note 3: $V_{DD} = -24~V$, $T_{ch} = 25^{\circ}C$ (initial), $L = 500~\mu H$, $R_G = 25~\Omega$, $I_{AR} = -18~A$

Note 4: Repetitive rating: pulse width limited by maximum channel temperature

Note 5: • on lower left of the marking indicates Pin 1.

Weekly code: (Three digits)
 Week of manufacture

 (01 for the first week of a year: sequential number up to 52 or 53)

 Year of manufacture

 (The last digit of a year)

2

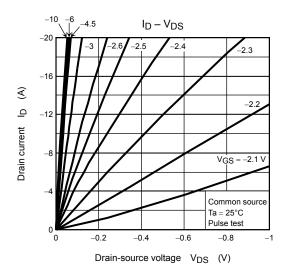
Electrical Characteristics (Ta = 25°C)

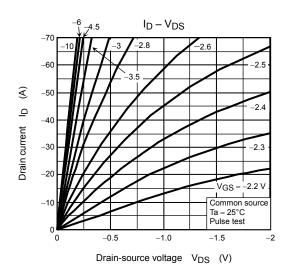
Chara	acteristics	Symbol	Symbol Test Condition Min Typ. Ma		Max	Unit	
Gate leakage curre	nt	I _{GSS}	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±100	nA
Drain cut-OFF curre	ent	I _{DSS}	$V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}$	_	_	-10	μА
Drain-source break	down voltage	V _{(BR)DSS}	$I_D = -10$ mA, $V_{GS} = 0$ V	-30	_		V
Diain-source break	down voitage	V _{(BR)DSX}	$I_D = -10 \text{ mA}, V_{GS} = 10V \text{ (Note 7)}$	-21	_		٧
Gate threshold volta	age	V _{th}	$V_{DS} = -10 \text{ V}, I_D = -1 \text{ mA}$	-0.8	_	-2.0	٧
Drain-source ON-resistance		D	$V_{GS} = -4.5 \text{ V}, I_D = -9 \text{ A}$		3.3	4.2	mΩ
Diam-source Oiv-re	sistance	R _{DS} (ON)	$V_{GS} = -10 \text{ V}, I_D = -9 \text{ A}$		2.6	3.2	11152
Forward transfer ad	transfer admittance Y _{fs}		$V_{DS} = -10 \text{ V}, I_D = -9 \text{ A}$	40	80		S
Input capacitance		C _{iss}	V _{DS} = -10 V, V _{GS} = 0 V, f = 1 MHz	_	7420	_	pF
Reverse transfer capacitance		C _{rss}		_	1180	_	
Reverse transfer capacitance Output capacitance		Coss		_	1440	_	
· · ·	Rise time	t _r	V _{CS} 0 V 7		10		
Switching time	Turn-ON time	t _{on}	VGS ₋₁₀ V I _D = -9 A ○ 出力	_	18	- ±10010102.0 3.3	- ns
Switching time	Fall time	t _f	4.7 \\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	_	275	_	
	Turn-OFF time	t _{off}	$V_{DD} \approx -15 \text{ V}$ Duty \leq 1%, $t_W = 10 \mu\text{s}$	_	790	_	
Total gate charge (gate-source plus g	ate-drain)	Qg $V_{DD} \approx -24 \text{ V. } V_{GS} = -10 \text{ V.}$ — 180 —		_			
Gate-source charge 1		Q _{gs1}	$I_D = -18 \text{ A}$	_	20	_	nC
Gate-drain ("miller")	charge	Q _{gd}		_	40		

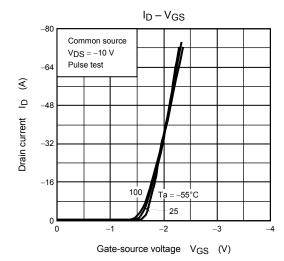
Source-Drain Ratings and Characteristics (Ta = 25°C)

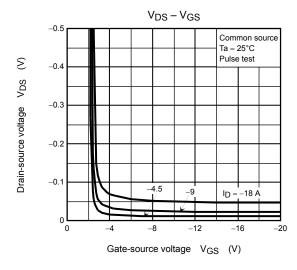
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit	
Drain reverse current	Pulse	(Note 1)	I _{DRP}	_	_	_	-72	А
Forward voltage (diode)		V_{DSF}	$I_{DR} = -18 \text{ A}, V_{GS} = 0 \text{ V}$	_	_	1.2	V	

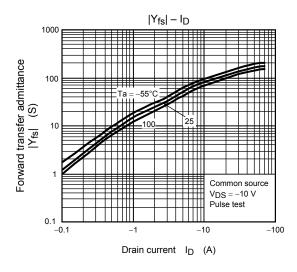
Note 7: V_{DSX} mode (the application of a plus voltage between gate and source) may cause decrease in maximum rating of drain-source voltage.

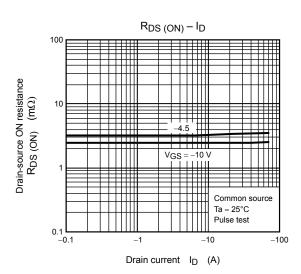


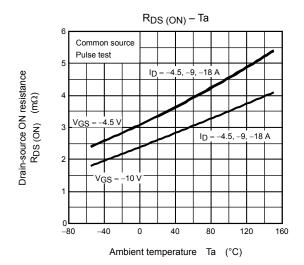


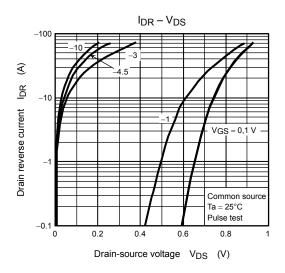


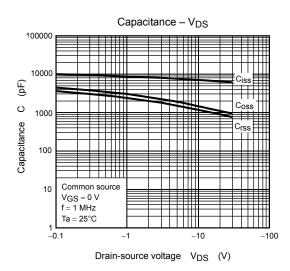


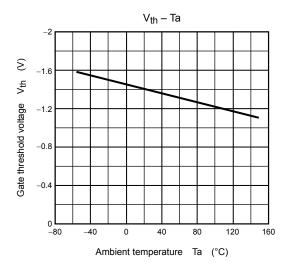


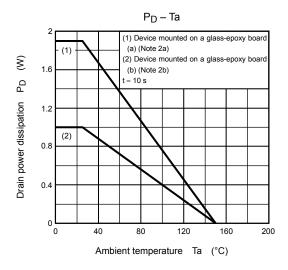


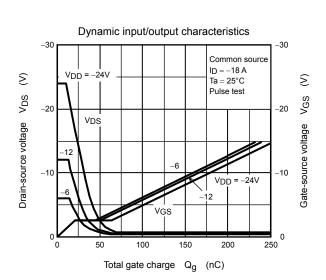


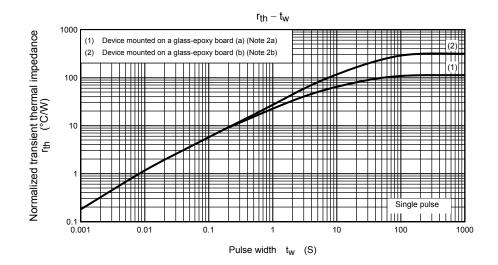


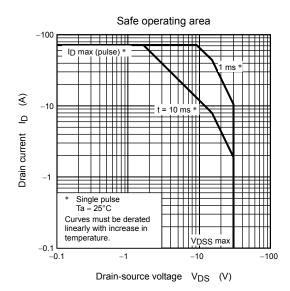












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